

# DATA SHEET

## **BTA216B series D, E and F** Three quadrant triacs guaranteed commutation

Product specification

July 2018



**WeEn**

WeEn Semiconductors

# Three quadrant triacs guaranteed commutation

# BTA216B series D, E and F

## GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a plastic envelope suitable for surface mounting, intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

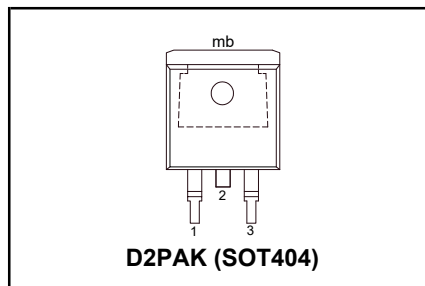
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{DRM}$	<b>BTA216B- BTA216B- BTA216B-</b> Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	<b>600D 600E 600F</b> 600	V
$I_{T(RMS)}$		16	A
$I_{TSM}$		140	A

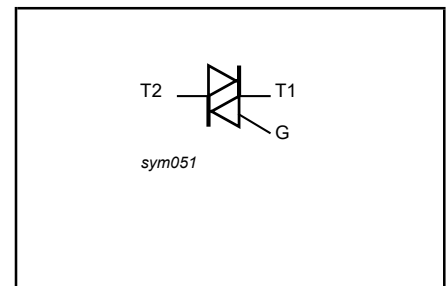
## PINNING - SOT404

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
mb	main terminal 2

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	600 <sup>1</sup>	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ }^{\circ}\text{C}$	-	16	A
$I_{TSM}$	Non-repetitive peak on-state current	full sine wave; $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge	-	140	A
$I^2t$	$I^2t$ for fusing	$t = 20\text{ ms}$	-	150	A <sup>2</sup> s
$di_T/dt$	Repetitive rate of rise of on-state current after triggering	$t = 16.7\text{ ms}$	-	98	A/ $\mu\text{s}$
		$t = 10\text{ ms}$	-	100	A/ $\mu\text{s}$
$I_{GM}$	Peak gate current	$I_{TM} = 20\text{ A}; I_G = 0.2\text{ A}; di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	2	A
$P_{GM}$	Peak gate power		-	5	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	Storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	Operating junction temperature		-	125	$^{\circ}\text{C}$

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu\text{s}$ .

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## BTA216B series D, E and F

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle minimum footprint, FR4 board	-	-	1.7	K/W
			-	55	-	K/W

### STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
<b>BTA216B-</b>							
$I_{GT}$	Gate trigger current <sup>2</sup>	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	-	...D	...E	...F	
			-	5	10	25	mA
			-	5	10	25	mA
			-	5	10	25	mA
$I_L$	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	-	15	25	30	mA
			-	25	30	40	mA
			-	25	30	40	mA
$I_H$	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	15	25	30	mA
<b>...D, E, F</b>							
$V_T$	On-state voltage	$I_T = 20\text{ A}$	-	1.5			V
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	1.5			V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A};$ $T_j = 125\text{ °C}$	0.25	-			V
$I_D$	Off-state leakage current	$V_D = V_{DRM(max)}; T_j = 125\text{ °C}$	-	0.5			mA

### DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			MAX.	UNIT
<b>BTA216B-</b>							
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110\text{ °C};$ exponential waveform; gate open circuit	...D	...E	...F	-	V/ $\mu$ s
			30	60	70	-	V/ $\mu$ s
$dI_{com}/dt$	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125\text{ °C};$ $I_{T(RMS)} = 16\text{ A};$ $dV_{com}/dt = 10\text{ V}/\mu\text{s};$ gate open circuit	2.5	6.2	18	-	A/ms
$dI_{com}/dt$	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125\text{ °C};$ $I_{T(RMS)} = 16\text{ A};$ $dV_{com}/dt = 0.1\text{ V}/\mu\text{s};$ gate open circuit	12	20	50	-	A/ms

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

Three quadrant triacs  
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BTA216B series D, E and F

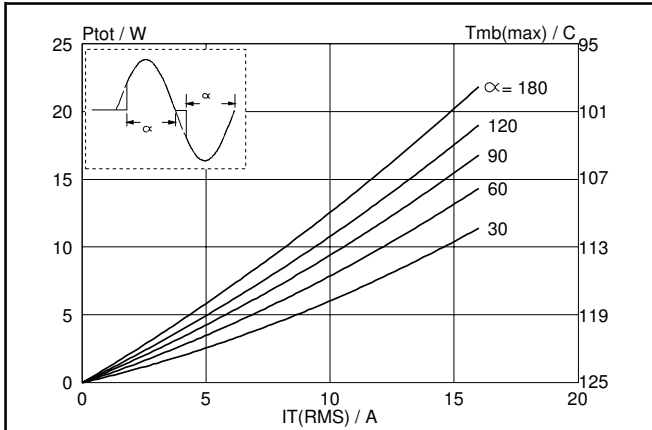


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

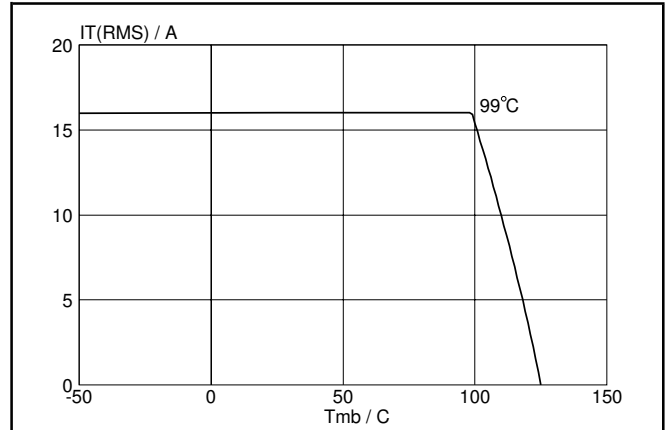


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

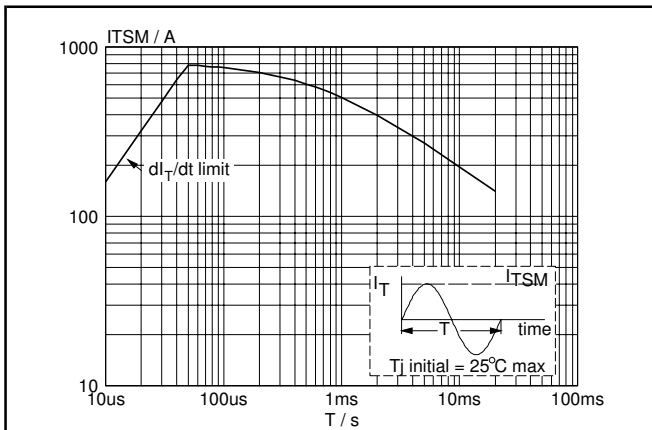


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20\text{ms}$ .

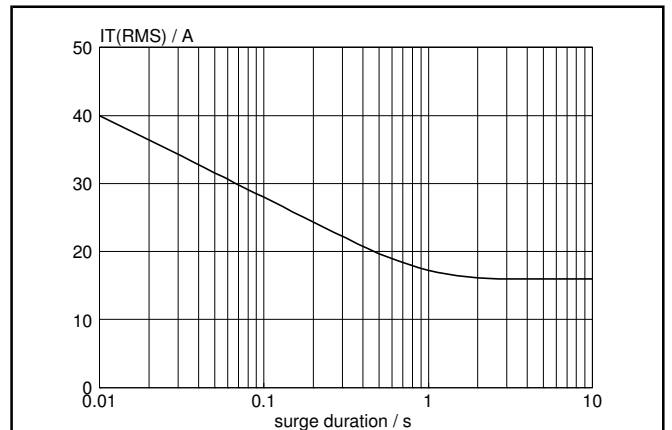


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50 \text{ Hz}$ ;  $T_{mb} \leq 99^\circ\text{C}$ .

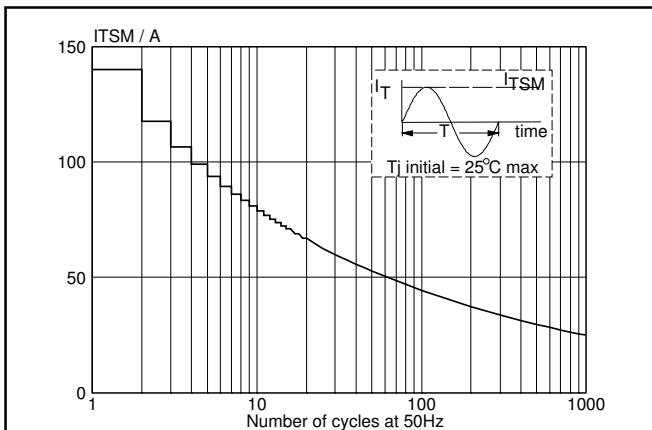


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50 \text{ Hz}$ .

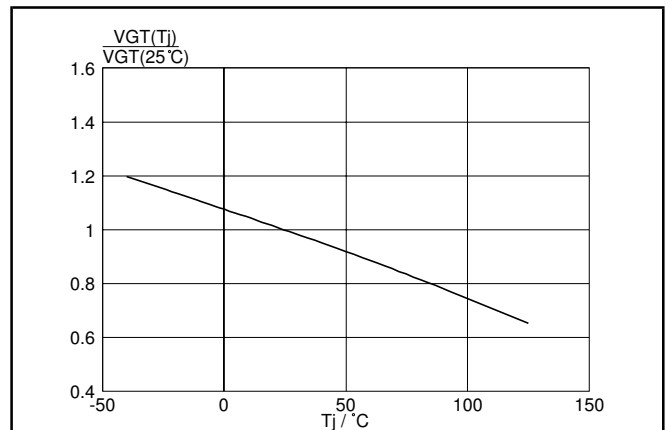
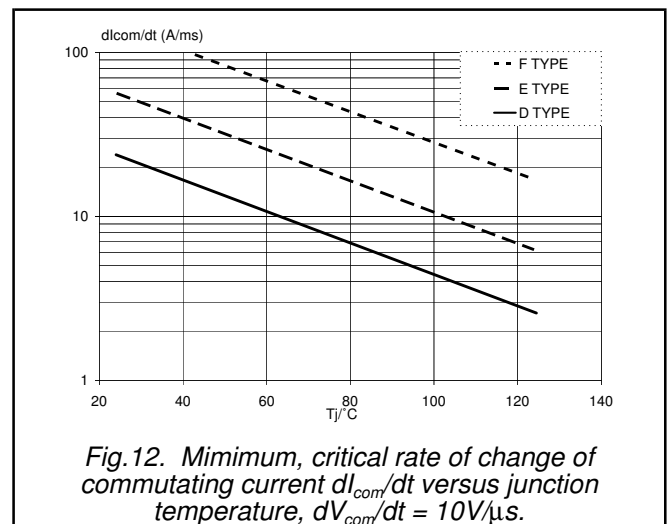
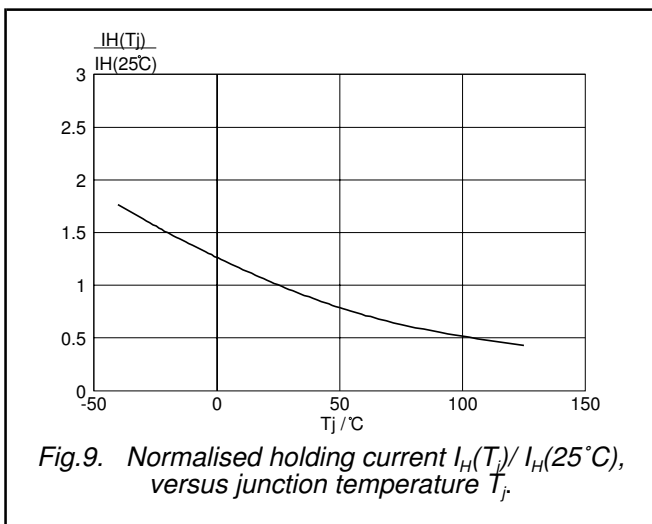
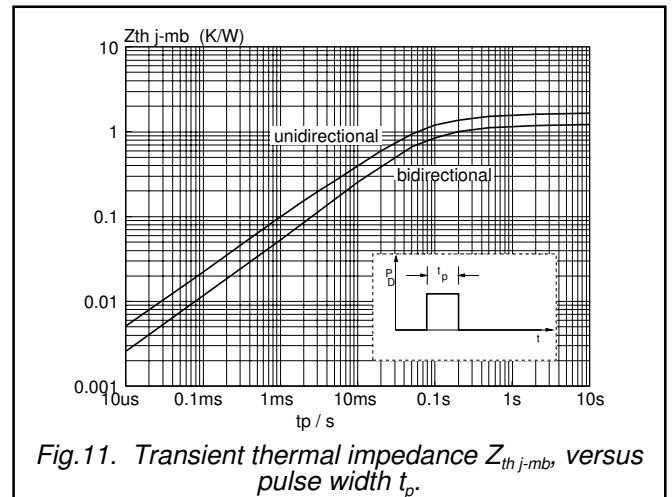
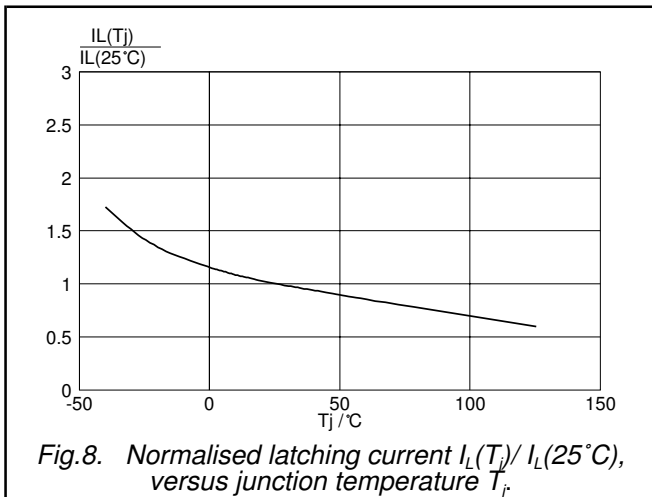
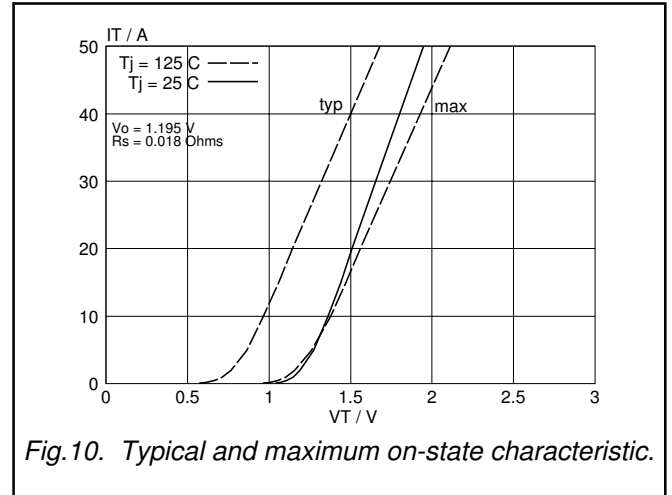
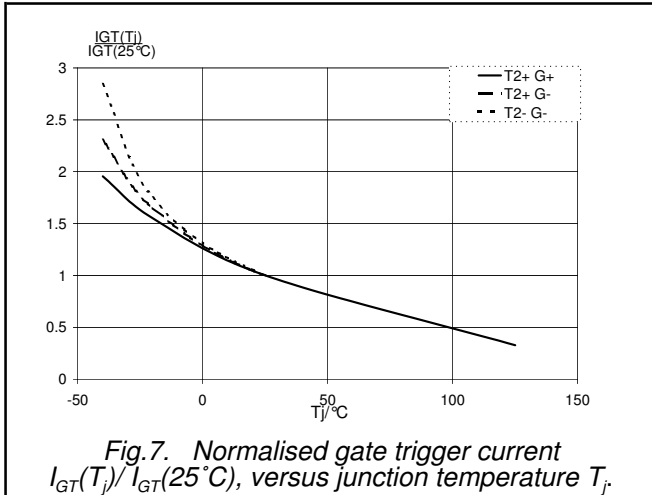


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

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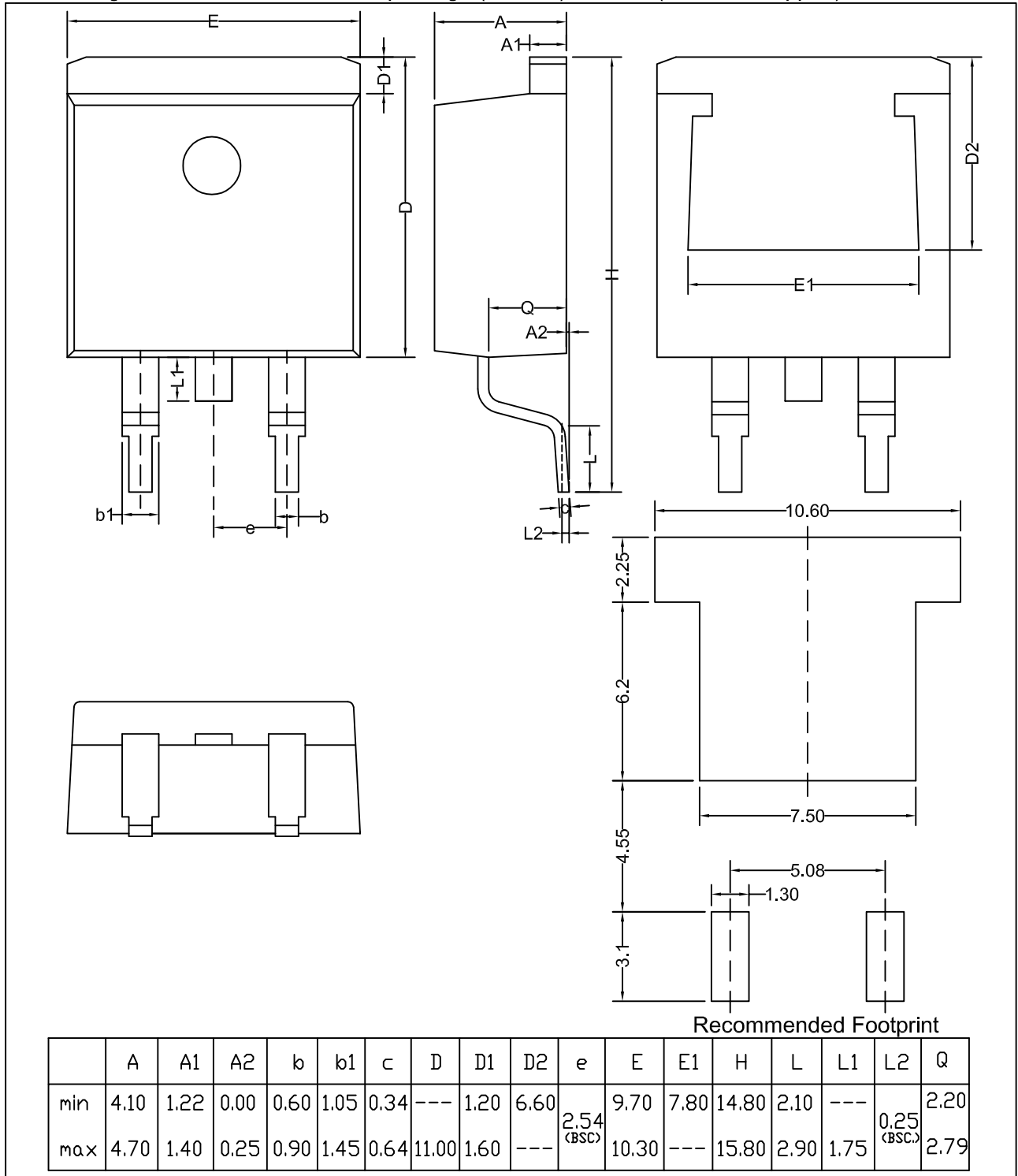
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**MECHANICAL DATA**

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

TO263



## Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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